

ABSTRACT

A semiconductor film formation method allowing a single-crystal semiconductor film to be formed at a desired position on a substrate with reliability is disclosed. After preparing the substrate having a non-single-crystal semiconductor film formed thereon and an optical mask having a predetermined pattern, a projection area of the optical mask is relatively positioned at the desired position on the substrate. Thereafter, the desired position of the non-single-crystal semiconductor film is irradiated with laser light through the optical mask to change an irradiated portion of the non-single-crystal semiconductor film to the single-crystal semiconductor film. Then, an insulation film is formed on at least the single-crystal semiconductor film.